## NPN Small-Signal Darlington Transistor

## BSP52T1G, BSP52T3G, SBSP52T1G

This NPN small signal Darlington transistor is designed for use in switching applications, such as print hammer, relay, solenoid and lamp drivers. The device is housed in the SOT-223 package, which is designed for medium power surface mount applications.

### **Features**

- The SOT-223 Package can be soldered using wave or reflow. The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- Available in 12 mm Tape and Reel
   Use BSP52T1 to Order the 7 Inch/1000 Unit Reel
- PNP Complement is BSP62T1
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

#### MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CES</sub>	80	V
Collector-Base Voltage	V <sub>CBO</sub>	90	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current	I <sub>C</sub>	1.0	Α
Total Power Dissipation (Note 1) @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	0.8 6.4	W mW/°C
Total Power Dissipation (Note 2) @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.25 10	W mW/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to 150	°C

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance (Note 1) Junction-to-Ambient	$R_{\theta JA}$	156	°C/W
Thermal Resistance (Note 2) Junction-to-Ambient	$R_{\theta JA}$	100	°C/W
Maximum Temperature for Soldering Purposes Time in Solder Bath	TL	260 10	°C Sec

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

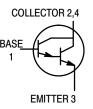
- Device mounted on a FR-4 glass epoxy printed circuit board using minimum recommended footprint.
- 2. Device mounted on a FR-4 glass epoxy printed circuit board using 1 cm<sup>2</sup> pad.



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# MEDIUM POWER NPN SILICON SURFACE MOUNT DARLINGTON TRANSISTOR



### **MARKING DIAGRAM**



SOT-223 CASE 318E STYLE 1



A = Assembly Location

Y = Year W = Work Week

AS3 = Specific Device Code = Pb-Free Package

(Note: Microdot may be in either location)

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BSP52T1G, SBSP52T1G	SOT-223 (Pb-Free)	1000 / Tape & Reel
BSP52T3G	SOT-223 (Pb-Free)	4000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## ${\tt BSP52T1G,\,BSP52T3G,\,SBSP52T1G}$

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		
Collector-Base Breakdown Voltage ( $I_C = 100 \mu A$ , $I_E = 0$ )	V <sub>(BR)</sub> CBO	90	_	-	V
Emitter-Base Breakdown Voltage ( $I_E = 10 \mu A, I_C = 0$ )	V <sub>(BR)EBO</sub>	5.0	-	_	V
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 80 V, V <sub>BE</sub> = 0)	I <sub>CES</sub>	_	_	10	μΑ
Emitter-Base Cutoff Current $(V_{EB} = 4.0 \text{ V}, I_{C} = 0)$	I <sub>EBO</sub>	_	_	10	μΑ
ON CHARACTERISTICS (Note 3)					
DC Current Gain $(I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V})$ $(I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V})$	h <sub>FE</sub>	1000 2000	_ _	_ _	-
Collector-Emitter Saturation Voltage ( $I_C = 500 \text{ mA}, I_B = 0.5 \text{ mA}$ )	V <sub>CE(sat)</sub>	-	_	1.3	V
Base-Emitter Saturation Voltage ( $I_C = 500 \text{ mA}, I_B = 0.5 \text{ mA}$ )	V <sub>BE(sat)</sub>	_	_	1.9	V
SWITCHING CHARACTERISTICS					
Rise Time (V <sub>CC</sub> = 10 V, I <sub>C</sub> = 150 mA, I <sub>B1</sub> = 0.15 mA)	t <sub>r</sub>	_	155	_	ns
Delay Time $(V_{CC} = 10 \text{ V}, I_C = 150 \text{ mA}, I_{B1} = 0.15 \text{ mA})$	t <sub>d</sub>	-	205	-	ns
Storage Time $(V_{CC} = 10 \text{ V}, I_C = 150 \text{ mA}, I_{B1} = 0.15 \text{ mA}, I_{B2} = 0.15 \text{ mA})$	t <sub>s</sub>	-	420	-	ns
Fall Time $(V_{CC} = 10 \text{ V}, I_{C} = 150 \text{ mA}, I_{B1} = 0.15 \text{ mA}, I_{B2} = 0.15 \text{ mA})$	t <sub>f</sub>	_	365	_	ns

<sup>3.</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

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## TYPICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

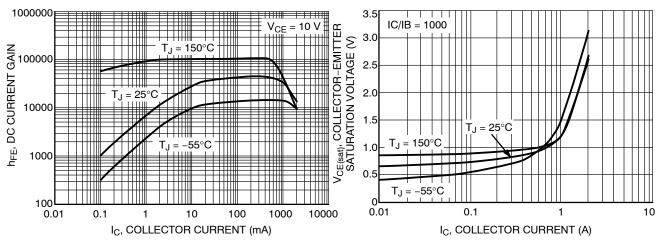


Figure 1. DC Current Gain

Figure 2. Collector-Emitter Saturation Voltage

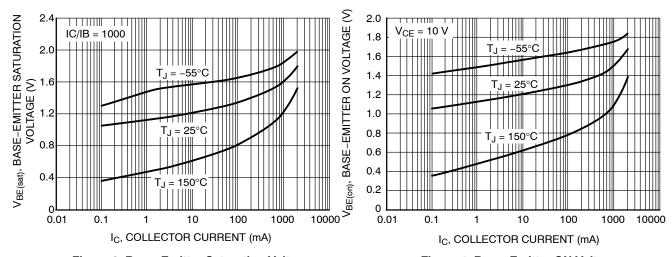


Figure 3. Base-Emitter Saturation Voltage

Figure 4. Base-Emitter ON Voltage

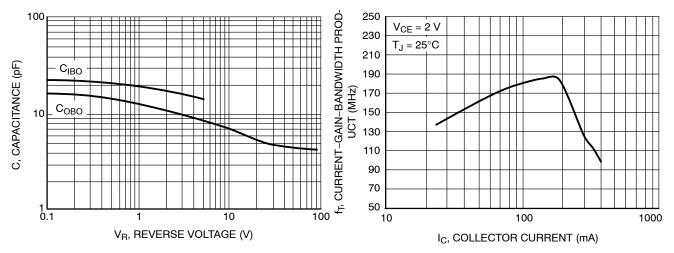


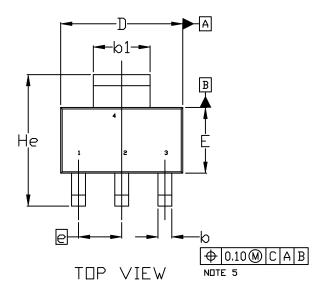
Figure 5. Capacitance

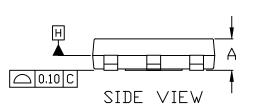
Figure 6. Current Gain Bandwidth Product vs. Collector Current

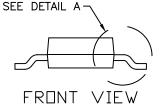


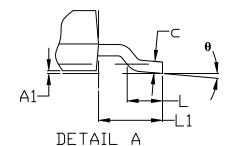
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**DATE 02 OCT 2018** 





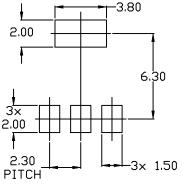




#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
  MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5. ALLIS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	1.50	1.63	1.75	
A1	0.02	0.06	0.10	
Ø	0.60	0.75	0.89	
b1	2.90	3.06	3.20	
U	0.24	0.29	0.35	
D	6.30	6.50	6.70	
E	3.30	3.50	3.70	
е	2.30 BSC			
L	0.20			
L1	1.50	1.75	2.00	
He	6.70	7.00	7.30	
θ	0°		10°	



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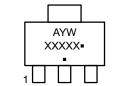
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**DATE 02 OCT 2018** 

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

# GENERIC MARKING DIAGRAM\*



A = Assembly Location

Y = Year W = Work Week

not follow the Generic Marking.

XXXXX = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location)
\*This information is generic. Please refer to
device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "•", may
or may not be present. Some products may

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